

216780US-2-DIV

3 / Prel. amdt.
B
E. Willis
3-25-02

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF :
SATOSHI SHIMIZU ET AL : ATTN: APPLICATION DIVISION
SERIAL NO: NEW U.S. APPLICATION :
FILED: HEREWITH :
FOR: MIS TRANSISTOR AND METHOD:
OF FABRICATING THE SAME

PRELIMINARY AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

Prior to a first examination on the merits, please amend the above-identified application as follows:

IN THE SPECIFICATION

Please amend the specification as shown in the marked-up copy following this amendment.

Please replace the paragraph at page 2, lines 8-16, with the following text:

B1 Then, this structure is heated under a proper atmosphere for forming silicide films 10 by the silicon substrate 1 and the polycrystalline silicon forming the gate electrode 5 (see Fig. 49). The composition of these silicide films 10 is expressed as MSix, assuming that M represents a metal element forming the metal film 9, for example, where x represents the ratio of silicon atoms to the metal atoms. In this case, a short-time heat treatment (rapid thermal annealing) is generally performed through a lamp annealing furnace. The heat